CONTENTS

Preface vii

OXIDATION OF SILICON

Thermal oxidation of silicon: new experimental results and models
E.A. Irene and R. Ghez 1

Effect of silicon surface cleaning procedures on oxidation kinetics and surface chemistry
J.M. deLarios, C.R. Helms, D.B. Kao and B.E. Deal 17

High temperature reaction and defect chemistry at the Si/SiO_2 interface
K. Hofmann, G.W. Rubloff, M. Liehr and D.R. Young 25

Constant current versus constant voltage plasma anodization techniques
R.B. Beck 32

Oxidation of silicon in the afterglow of microwave induced plasmas
C. Vinckier, P. Coeckelberghs, G. Stevens and S. De Jaegere 40

Effects of low temperature annealing on the electrical properties of plasma grown oxides
K.J. Barlow, W. Eccleston and S. Taylor 47

COMPOUND SEMICONDUCTORS

Charge trapping in n-$Al_xGa_{1-x}As$ "insulators" and related device instabilities
T.N. Theis and B.D. Parker 52

Photo-stimulated CVD of SiN_x for GaAs IC applications
N. Arnold and L. Schleicher 64

Ion beam enhanced deposition of AlN_xO_y alloys on InP
C. Santinelli, R. Blanchet, P. Viktorovitch and F. Benyahia 69

Dielectrics for passivation of planar InP/InGaAs diodes
G. Unterbörsch, H.G. Bach, F. Schmitt, R. Schmidt and W. Schlaak 76

InP native oxide: a drift factor in InP–MIS
V.V.Pham, D. Esteve, J. Farré, A. El Mahdy, M. Ronda and J.J. Simonne 83

Reduction of the concentration of slow insulator states in SiO_2/InP–MIS structures
W. Kulisch, H. Rombach and R. Kassing 89

Comparative effects of polymide and PECVD silicon nitride as passivating layers on GaAs power MESFET characteristics
G.P. Donzelli and B. Gabbrielli 95

InGaAs/Si_3N_4 interface obtained in ultrahigh vacuum multipolar plasma: in-situ control by ellipsometry and electrical characterization
P. Boher, M. Renaud, J.M. Lopez-Villegas, J. Schneider and J.P. Chane 100

Photoluminescence transient response as a tool to "track" the origin of drift phenomena at the InP/insulator interface
S.K. Krawczyk and K. Schohe 108

CHARACTERIZATION OF INSULATOR–SEMICONDUCTOR STRUCTURES

Determination of Si–SiO_2 interface trap properties of p-MOS structures with very thin oxides by conductance measurement
K.K. Hung and Y.C. Cheng 114

Time-dependent response of interface states determined by using differential isothermal transient spectroscopy
J. Esteve, J. Samitier, H. Altelarrea, A. Herms and J.R. Morante 120

A new method to determine Si/SiO_2 interface recombination parameters using a gate-controlled point-junction diode under illumination
R. Girisch, R.P. Mertens and R.F. De Keersmaecker 127

Low-temperature ESR study of P_{b0} defects residing in the (111) Si/native oxide interface
A. Stesmans 134

Electrical switching and noise spectrum of Si–SiO_2 interface defects generated by hot electrons
M. Bollu, F. Koch, A. Madenach and J. Scholz 142

Individual interface states and their implications for low-frequency noise in MOSFETs
M.J. Kirton, M.J. Uren and S. Collins 148

MULTILAYER DIELECTRICS

A new model for the discharge behaviour of metal–nitride–oxide–silicon (MNOS) non-volatile memory devices
G.L. Heyns and H.E. Maes 153

Amphoteric trap modeling of multidielectric scaled SONOS nonvolatile memory structures
F.R. Libsch, A. Roy and M.H. White 160

Charge transport and trapping model for scaled nitride–oxide stacked films
K.K. Young, C. Hu and W.G. Oldham 171

Interfacial tunneling barrier heights in triple-layer dielectrics
R. Baunach and A. Spitzer 180

NITRIDES AND OXYNITRIDES

Characterization of LPCVD and PECVD silicon oxynitride films
F.H.P.M. Habraken 186

Hydrogen distribution in oxynitride/oxide structures
J.B. Oude Elferink, U.A. van der Heide, W.M. Arnold Bik, F.H.P.M. Habraken and W.F. van der Weg 197

Electrical properties of thin PECVD silicon oxynitride films
L. Do Thanh, V. Exner and P. Balk 204

Analysis of thin thermal silicon nitride films on silicon
M.A. Sobolewski and C.R. Helms 210

High and low thermal nitridation of SiO_2 thin films
B. Balland, J.C. Bureau, A. Benamar, A. Ronda and A. Glachant 216

Nitridation of thin SiO_2 films in N_2 and NH_3 plasmas
P. Fazan, M. Dutoit and M. Ilegems 224

High field phenomena in thin plasma nitrided SiO_2 films
M. El-Sayed and J. Camargo Da Costa 229

Electrical conduction in thin thermally nitrided SiO_2 (nitroxide)
X.R. Cheng, B.Y. Liu and Y.C. Cheng 237

IMPURITIES IN SiO_2

Diffusion of Group III and V elements in SiO_2
A.H. van Ommen 244

Ion implantation induced stoichiometric imbalance in SiO_2
M. Offenberg and P. Balk 265

Hole capture in SiO_2 films after ion implantation
H. Neitzert, M. Offenberg and P. Balk 272

CONDUCTION IN INSULATORS

Hot electrons in silicon dioxide: ballistic to steady-state transport
D.J. DiMaria and M.V. Fischetti 278

Valence band electron tunneling in metal–oxide–silicon structures
A. Modelli 298

Interface states and impurities in MOS structures with very thin tunneling barriers
P. Balk, L. Do Thanh, S. Ewert, M. Kuball and S. Schmitz 304

INSULATOR DEGRADATION

Models and experiments on degradation of oxidized silicon (Extended Abstract)
C.T. Sah 311

Evaluation of channel hot carrier effects in n-MOS transistors at 77 K with the charge pumping technique
P. Heremans, Y.-C. Sun, G. Groeseneken and H.E. Maes 313

On the nature and energy distribution of defect states caused by hot electrons in Si
A. Asenov, M. Bollu, F. Koch and J. Scholz 319

The statistics of dielectric breakdown in MOS capacitors under static and dynamic voltage stress
S.K. Haywood, M.M. Heyns and R.F. De Keersmaecker 325

Charge trapping and breakdown in thin SiO_2 polysilicon-gate MOS capacitors
M. Dutoit, P. Fazan, A. Benjelloun, M. Ilegems and J.-M. Moret 333

Improvement of the Si–SiO_2 interface stress resistance of thin gate oxides after channel ion implantation
R.B. Calligaro 339

Charge storage in MOS structures as affected by avalanche- and photoinjection
S.N. Kuznetsov and V.A. Gurtov 347

POLYSILICON

Material properties and characteristics of polysilicon transistors for large area electronics
P. Migliorato and D.B. Meakin 353

Low defect-density polycrystalline silicon for high performance thin film transistors
D.B. Meakin, N.A. Economou, P.A. Coxon, J. Stoemenos, A. Lowe and P. Migliorato 372

SEMICONDUCTOR-ON-INSULATOR

Buried oxide formation in Si by high-dose implantation of oxygen
A.H. van Ommen and M.P.A. Viegers 383

Optical and compositional studies of buried oxide layers in silicon formed by high dose implantation
R.J. Chater, J.A. Kilner, E. Scheid, S. Cristoloveneau, P.L.F. Hemment and K.J. Reeson 390

Some material structural properties of SOI substrates produced by SDB technology
Li Hui, Sun Guo-Liang, Zhan Juan and Tong Qin-Yi 397

Properties of graded Group IIa fluoride buffer layers for semiconductor heteroepitaxy
H. Zogg and S. Blunier 402

Author index 408

Subject index 413